

Hidenori Hiramatsu

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

179
papers

7,948
citations

45
h-index

84
g-index

197
ext. papers

8,701
ext. citations

4.4
avg, IF

5.8
L-index

#	Paper	IF	Citations
179	Degenerated Hole Doping and Ultra-Low Lattice Thermal Conductivity in Polycrystalline SnSe by Nonequilibrium Isovalent Te Substitution.. <i>Advanced Science</i> , 2022 , e2105958	13.6	1
178	Large phonon drag thermopower boosted by massive electrons and phonon leaking in LaAlO/LaNiO/LaAlO heterostructure. <i>Nano Letters</i> , 2021 , 21, 9240-9246	11.5	0
177	Reversible 3D-2D structural phase transition and giant electronic modulation in nonequilibrium alloy semiconductor, lead-tin-selenide. <i>Science Advances</i> , 2021 , 7,	14.3	3
176	Double Charge Polarity Switching in Sb-Doped SnSe with Switchable Substitution Sites. <i>Advanced Functional Materials</i> , 2021 , 31, 2008092	15.6	5
175	Critical temperature and critical current density of hydrogen-doped SmFeAsO epitaxial films fabricated by thermal annealing with binary hydrides. <i>Applied Physics Express</i> , 2020 , 13, 073002	2.4	1
174	Extraordinary Strong Band-Edge Absorption in Distorted Chalcogenide Perovskites. <i>Solar Rrl</i> , 2020 , 4, 1900555	7.1	31
173	Growth, Properties, and Device Fabrication of Iron-Based Superconductor Thin-Films 2020 , 213-241		
172	Coexistence of magnetism and superconductivity in thin films of the Fe-based superconductor BaLaFeAs. <i>Journal of Physics Condensed Matter</i> , 2020 , 32, 485804	1.8	2
171	Strain Engineering at Heterointerfaces: Application to an Iron Pnictide Superconductor, Cobalt-Doped BaFeAs. <i>ACS Applied Materials & Interfaces</i> , 2020 , 12, 50096-50104	9.5	2
170	Tunable Light Emission through the Range 1.8-3.2 eV and p-Type Conductivity at Room Temperature for Nitride Semiconductors, Ca(MgZn)N (= 0-1). <i>Inorganic Chemistry</i> , 2019 , 58, 12311-12316	5.1	6
169	New Amorphous InGaZnO Thin-Film Transistor-Based Optical Pixel Sensor for Optical Input Signal With Short Wavelength. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 3841-3846	2.9	1
168	Insulator-like behavior coexisting with metallic electronic structure in strained FeSe thin films grown by molecular beam epitaxy. <i>Physical Review B</i> , 2019 , 99,	3.3	3
167	Material Design of Green-Light-Emitting Semiconductors: Perovskite-Type Sulfide SrHfS. <i>Journal of the American Chemical Society</i> , 2019 , 141, 5343-5349	16.4	29
166	Particulate Generation on Surface of Iron Selenide Films by Air Exposure. <i>Journal of Superconductivity and Novel Magnetism</i> , 2019 , 32, 3047-3055	1.5	3
165	Stabilization and heteroepitaxial growth of metastable tetragonal FeS thin films by pulsed laser deposition. <i>Superconductor Science and Technology</i> , 2019 , 32, 054002	3.1	2
164	Low anisotropic upper critical fields in SmO _{1-x} F _x FeAs thin films with a layered hybrid structure. <i>Superconductor Science and Technology</i> , 2019 , 32, 044003	3.1	11
163	Transition Metal-Doped Amorphous Oxide Semiconductor Thin-Film Phosphor, Chromium-Doped Amorphous Gallium Oxide. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1800198	1.6	4

162	Heteroepitaxial Thin-Film Growth of a Ternary Nitride Semiconductor CaZn ₂ N ₂ . <i>ACS Applied Electronic Materials</i> , 2019 , 1, 1433-1438	4	7
161	Performance boosting strategy for perovskite light-emitting diodes. <i>Applied Physics Reviews</i> , 2019 , 6, 031402	17.3	63
160	Amorphous Oxide Semiconductor Thin-Film Transistors 2019 , 573-587		3
159	Exotic Crystal Structures and Electronic Structures in Novel Structured Inorganic Materials 2019 , 107-120		
158	Efficient construction method for phase diagrams using uncertainty sampling. <i>Physical Review Materials</i> , 2019 , 3,	3.2	16
157	Superconductivity at 48 K of heavily hydrogen-doped SmFeAsO epitaxial films grown by topotactic chemical reaction using CaH ₂ . <i>Physical Review Materials</i> , 2019 , 3,	3.2	9
156	Superconducting transition temperatures in the electronic and magnetic phase diagrams of SrVFeAsO, a superconductor. <i>Journal of Physics Condensed Matter</i> , 2019 , 31, 115801	1.8	6
155	Multiple Color Inorganic Thin-Film Phosphor, RE-Doped Amorphous Gallium Oxide (RE = Rare Earth: Pr, Sm, Tb, and Dy), Deposited at Room Temperature. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1700833	1.6	11
154	Effects of Base Pressure on Growth and Optoelectronic Properties of Amorphous In-Ga-Zn-O: Ultralow Optimum Oxygen Supply and Bandgap Widening. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019 , 216, 1700832	1.6	11
153	Recent advances in iron-based superconductors toward applications. <i>Materials Today</i> , 2018 , 21, 278-302	21.8	200
152	Pulsed laser deposition of SmFeAsO _{1-x} on MgO(100) substrates. <i>Applied Surface Science</i> , 2018 , 437, 418-428	4.8	8
151	Multiple states and roles of hydrogen in p-type SnS semiconductors. <i>Physical Chemistry Chemical Physics</i> , 2018 , 20, 20952-20956	3.6	6
150	Phase transition in CaFeAsH: bridging 1111 and 122 iron-based superconductors. <i>Dalton Transactions</i> , 2018 , 47, 12964-12971	4.3	1
149	Fabrication, Characterization, and Modulation of Functional Nanolayers 2018 , 207-235		1
148	Multiple Roles of Hydrogen Treatments in Amorphous InGaZnO Films. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, P365-P372	2	19
147	Highly hydrogen-sensitive thermal desorption spectroscopy system for quantitative analysis of low hydrogen concentration (~1 × 10 ¹⁰ atoms/cm) in thin-film samples. <i>Review of Scientific Instruments</i> , 2017 , 88, 053103	1.7	12
146	Amorphous Gallium Oxide as an Improved Host for Inorganic Light-Emitting Thin Film Semiconductor Fabricated at Room Temperature on Glass. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, P410-P414	2	6
145	Conversion of an ultra-wide bandgap amorphous oxide insulator to a semiconductor. <i>NPG Asia Materials</i> , 2017 , 9, e359-e359	10.3	56

144	Effects of working pressure and annealing on bulk density and nanopore structures in amorphous InGaZnO thin-film transistors. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 03BB03	1.4	9
143	$\text{BaFe}_2(\text{As}_{1-x}\text{Px})_2$ ($x=0.22\text{--}0.42$) thin films grown on practical metal-oxide substrates and their critical current densities. <i>Superconductor Science and Technology</i> , 2017 , 30, 044003	3.1	9
142	Key Factors for Insulator-Superconductor Transition in FeSe Thin Films by Electric Field. <i>IEEE Transactions on Applied Superconductivity</i> , 2017 , 27, 1-5	1.8	10
141	Exploration of Stable Strontium Phosphide-Based Electrides: Theoretical Structure Prediction and Experimental Validation. <i>Journal of the American Chemical Society</i> , 2017 , 139, 15668-15680	16.4	57
140	Thin-film Growth and Device Fabrication of Iron-based Superconductors. <i>TEION KOGAKU (Journal of Cryogenics and Superconductivity Society of Japan)</i> , 2017 , 52, 433-442	0.1	1
139	Structure determination in thin film $\text{Ba}_{1-x}\text{La}_x\text{Fe}_2\text{As}_2$: Relation between the FeAs_4 geometry and superconductivity. <i>Physical Review B</i> , 2017 , 96,	3.3	4
138	P-13: Quantitative Analysis and Deconvolution of Subgap States in Amorphous In-Ga-Zn-O. <i>Digest of Technical Papers SID International Symposium</i> , 2017 , 48, 1273-1275	0.5	1
137	P-187: Electronic Structures of Various Color Light-Emitting Amorphous Oxide Semiconductor Thin Films. <i>Digest of Technical Papers SID International Symposium</i> , 2017 , 48, 1974-1976	0.5	2
136	High-field transport properties of a P-doped BaFeAs film on technical substrate. <i>Scientific Reports</i> , 2017 , 7, 39951	4.9	29
135	An Exceptionally Narrow Band-Gap (~ 4 eV) Silicate Predicted in the Cubic Perovskite Structure: BaSiO . <i>Inorganic Chemistry</i> , 2017 , 56, 10535-10542	5.1	12
134	Electron effective mass and mobility limits in degenerate perovskite stannate BaSnO_3 . <i>Physical Review B</i> , 2017 , 95,	3.3	33
133	Transparent amorphous oxide semiconductor thin film phosphor, In-Mg-O:Eu . <i>Journal of the Ceramic Society of Japan</i> , 2016 , 124, 532-535	1	9
132	Discovery of earth-abundant nitride semiconductors by computational screening and high-pressure synthesis. <i>Nature Communications</i> , 2016 , 7, 11962	17.4	133
131	In-situ growth of superconducting SmOFeAs thin films by pulsed laser deposition. <i>Scientific Reports</i> , 2016 , 6, 35797	4.9	21
130	Enhanced critical-current in P-doped BaFeAs thin films on metal substrates arising from poorly aligned grain boundaries. <i>Scientific Reports</i> , 2016 , 6, 36828	4.9	26
129	Ultrawide band gap amorphous oxide semiconductor, GaZnO . <i>Thin Solid Films</i> , 2016 , 614, 84-89	2.2	12
128	Effects of thermal annealing on elimination of deep defects in amorphous InGaZnO thin-film transistors. <i>Thin Solid Films</i> , 2016 , 614, 73-78	2.2	11
127	Electric field-induced superconducting transition of insulating FeSe thin film at 35 K. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2016 , 113, 3986-90	11.5	73

126	Novel solid-phase epitaxy for multi-component materials with extremely high vapor pressure elements: An application to KFe ₂ As ₂ . <i>Applied Physics Express</i> , 2016 , 9, 055505	2.4	7
125	Room-temperature fabrication of light-emitting thin films based on amorphous oxide semiconductor. <i>AIP Advances</i> , 2016 , 6, 015106	1.5	10
124	Amorphous pnictide semiconductor BaZn ₂ As ₂ exhibiting high hole mobility. <i>Applied Physics Letters</i> , 2016 , 109, 242105	3.4	1
123	Recent progress in pulsed laser deposition of iron based superconductors. <i>Journal Physics D: Applied Physics</i> , 2016 , 49, 345301	3	15
122	Solid phase epitaxial growth of high mobility La:BaSnO ₃ thin films co-doped with interstitial hydrogen. <i>Applied Physics Letters</i> , 2016 , 108, 172101	3.4	27
121	SnS thin films prepared by H ₂ S-free process and its p-type thin film transistor. <i>AIP Advances</i> , 2016 , 6, 015112	1.5	11
120	Nonequilibrium Rock-Salt-Type Pb-Doped SnSe with High Carrier Mobilities 1300 cm ² /(Vs). <i>Chemistry of Materials</i> , 2016 , 28, 2278-2286	9.6	13
119	Exploration of new superconductors and functional materials, and fabrication of superconducting tapes and wires of iron pnictides. <i>Science and Technology of Advanced Materials</i> , 2015 , 16, 033503	7.1	141
118	n-type conversion of SnS by isovalent ion substitution: Geometrical doping as a new doping route. <i>Scientific Reports</i> , 2015 , 5, 10428	4.9	44
117	Vortex Pinning Properties of Phosphorous-Doped $\text{BaFe}_{2}\text{As}_{2}$ Epitaxial Films: Comparison Between $(\text{La},\text{Sr})(\text{Al},\text{Ta})\text{O}_{3}$ and MgO Substrates. <i>IEEE Transactions on Applied Superconductivity</i> , 2015 , 25, 1-5	1.8	6
116	. <i>Journal of Display Technology</i> , 2015 , 11, 518-522		20
115	. <i>Journal of Display Technology</i> , 2015 , 11, 523-527		22
114	Fabrication and opto-electrical properties of amorphous (Zn,B)O thin film by pulsed laser deposition. <i>Journal of the Ceramic Society of Japan</i> , 2015 , 123, 523-526	1	1
113	Effects of sulfur substitution in amorphous InGaZnO ₄ : optical properties and first-principles calculations. <i>Journal of the Ceramic Society of Japan</i> , 2015 , 123, 537-541	1	6
112	Effects of residual hydrogen in sputtering atmosphere on structures and properties of amorphous In-Ga-Zn-O thin films. <i>Journal of Applied Physics</i> , 2015 , 118, 205703	2.5	28
111	Heteroepitaxial growth of SnSe films by pulsed laser deposition using Se-rich targets. <i>Journal of Applied Physics</i> , 2015 , 118, 205302	2.5	27
110	Detection of dead layers and defects in polycrystalline Cu ₂ O thin-film transistors by x-ray reflectivity and photoresponse spectroscopy analyses. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015 , 33, 051211	1.3	8
109	Growth of high-quality SnS epitaxial films by H ₂ S flow pulsed laser deposition. <i>Applied Physics Letters</i> , 2014 , 104, 072106	3.4	27

108	Narrow bandgap in BaZnAs_2 and its chemical origins. <i>Journal of the American Chemical Society</i> , 2014 , 136, 14959-65	16.4	25
107	Growth of c-axis-oriented superconducting KFeAs thin films. <i>ACS Applied Materials & Interfaces</i> , 2014 , 6, 14293-301	9.5	11
106	Epitaxial growth and electronic structure of a layered zinc pnictide semiconductor, BaZn_2As_2 . <i>Thin Solid Films</i> , 2014 , 559, 100-104	2.2	10
105	Fabrication and characterization of $\text{ZnS}:(\text{Cu},\text{Al})$ thin film phosphors on glass substrates by pulsed laser deposition. <i>Thin Solid Films</i> , 2014 , 559, 18-22	2.2	10
104	Electric double-layer transistor using layered iron selenide Mott insulator $\text{TlFe}_{1.6}\text{Se}_2$. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2014 , 111, 3979-83	11.5	26
103	. <i>Journal of Display Technology</i> , 2014 , 10, 979-983		15
102	High critical-current density with less anisotropy in $\text{BaFe}_2(\text{As},\text{P})_2$ epitaxial thin films: Effect of intentionally grown c-axis vortex-pinning centers. <i>Applied Physics Letters</i> , 2014 , 104, 182603	3.4	41
101	Roles of Hydrogen in Amorphous Oxide Semiconductor In-Ga-Zn-O: Comparison of Conventional and Ultra-High-Vacuum Sputtering. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, Q3085-Q3090	3.7	43
100	Critical factor for epitaxial growth of cobalt-doped BaFe_2As_2 films by pulsed laser deposition. <i>Applied Physics Letters</i> , 2014 , 104, 172602	3.4	22
99	The atomic structure, band gap, and electrostatic potential at the $(112)[11\bar{0}]$ twin grain boundary of CuInSe_2 . <i>Applied Physics Letters</i> , 2014 , 104, 153904	3.4	14
98	SnAs with the NaCl-type Structure: Type-I Superconductivity and Single Valence State of Sn. <i>Chemistry of Materials</i> , 2014 , 26, 7209-7213	9.6	25
97	Film Texture, Hole Transport and Field-Effect Mobility in Polycrystalline SnO Thin Films on Glass. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, Q3040-Q3044	2	28
96	Thin film growth of Fe-based superconductors: from fundamental properties to functional devices. A comparative review. <i>Reports on Progress in Physics</i> , 2014 , 77, 046502	14.4	67
95	Indium-based ultraviolet-transparent electroconductive oxyfluoride InOF : ambient-pressure synthesis and unique electronic properties in comparison with In_2O_3 . <i>Journal of the American Chemical Society</i> , 2013 , 135, 13080-8	16.4	10
94	Unusual pressure effects on the superconductivity of indirectly electron-doped $(\text{Ba}_{1-x}\text{La}_x)\text{Fe}_2\text{As}_2$ epitaxial films. <i>Physical Review B</i> , 2013 , 88,	3.3	16
93	Superconducting Properties and Phase Diagram of Indirectly Electron-Doped $(\text{Sr}_{1-x}\text{La}_x)\text{Fe}_2\text{As}_2$ Epitaxial Films Grown by Pulsed Laser Deposition. <i>IEEE Transactions on Applied Superconductivity</i> , 2013 , 23, 7300405-7300405	1.8	13
92	Ultralow-Dissipative Conductivity by Dirac Fermions in BaFe_2As_2 . <i>Journal of the Physical Society of Japan</i> , 2013 , 82, 043709	1.5	8
91	Magnetic scattering and electron pair breaking by rare-earth-ion substitution in BaFe_2As_2 epitaxial films. <i>New Journal of Physics</i> , 2013 , 15, 073019	2.9	18

90	Anomalous scaling behavior in a mixed-state Hall effect of a cobalt-doped BaFe ₂ As ₂ epitaxial film with a high critical current density over 1 MA/cm ² . <i>Physical Review B</i> , 2013 , 87,	3.3	14
89	Hydrogen passivation of electron trap in amorphous In-Ga-Zn-O thin-film transistors. <i>Applied Physics Letters</i> , 2013 , 103, 202114	3.4	92
88	Microstructure and transport properties of [001]-tilt bicrystal grain boundaries in iron pnictide superconductor, cobalt-doped BaFe ₂ As ₂ . <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2012 , 177, 515-519	3.1	32
87	Structural relaxation in amorphous oxide semiconductor, a-In-Ga-Zn-O. <i>Journal of Applied Physics</i> , 2012 , 111, 073513	2.5	74
86	Thin Film Growth and Device Fabrication of Iron-Based Superconductors. <i>Journal of the Physical Society of Japan</i> , 2012 , 81, 011011	1.5	47
85	Role of lone pair electrons in determining the optoelectronic properties of BiCuOSe. <i>Physical Review B</i> , 2012 , 85,	3.3	37
84	Thin film growth by pulsed laser deposition and properties of 122-type iron-based superconductor AE(Fe _{1-x} Co _x) ₂ As ₂ (AE=alkaline earth). <i>Superconductor Science and Technology</i> , 2012 , 25, 084015	3.1	41
83	Competition and cooperation of pinning by extrinsic point-like defects and intrinsic strong columnar defects in BaFe ₂ As ₂ thin films. <i>Physical Review B</i> , 2012 , 86,	3.3	38
82	Solid-state source of atomic oxygen for low-temperature oxidation processes: application to pulsed laser deposition of TiO ₂ :N films. <i>Review of Scientific Instruments</i> , 2012 , 83, 023903	1.7	1
81	Identical effects of indirect and direct electron doping of superconducting BaFe ₂ As ₂ thin films. <i>Physical Review B</i> , 2012 , 85,	3.3	41
80	Advantageous grain boundaries in iron pnictide superconductors. <i>Nature Communications</i> , 2011 , 2, 409	17.4	212
79	Liquid vortex phase and strong-c-axis pinning in low anisotropy BaCo _x Fe _{2-x} As ₂ pnictide films. <i>Superconductor Science and Technology</i> , 2011 , 24, 055007	3.1	44
78	Terahertz conductivity measurement of FeSe _{0.5} Te _{0.5} and Co-doped BaFe ₂ As ₂ thin films. <i>Physica C: Superconductivity and Its Applications</i> , 2011 , 471, 634-638	1.3	8
77	Characterization of epitaxial Co-doped BaFe ₂ As ₂ thin films. <i>Physica C: Superconductivity and Its Applications</i> , 2011 , 471, 1181-1184	1.3	5
76	Biaxially textured cobalt-doped BaFe ₂ As ₂ films with high critical current density over 1 MA/cm ² on MgO-buffered metal-tape flexible substrates. <i>Applied Physics Letters</i> , 2011 , 98, 242510	3.4	105
75	Josephson junction in cobalt-doped BaFe ₂ As ₂ epitaxial thin films on (La,Sr)(Al,Ta)O ₃ bicrystal substrates. <i>Applied Physics Letters</i> , 2010 , 96, 142507	3.4	66
74	Transport and magnetic properties of Co-doped BaFe ₂ As ₂ epitaxial thin films grown on MgO substrate. <i>Superconductor Science and Technology</i> , 2010 , 23, 105016	3.1	18
73	DC superconducting quantum interference devices fabricated using bicrystal grain boundary junctions in Co-doped BaFe ₂ As ₂ epitaxial films. <i>Superconductor Science and Technology</i> , 2010 , 23, 082001	3.1	46

72	Origins of hole doping and relevant optoelectronic properties of wide gap p-type semiconductor, LaCuOSe. <i>Journal of the American Chemical Society</i> , 2010 , 132, 15060-7	16.4	36
71	High Critical Current Density 4 MA/cm ² in Co-Doped BaFe ₂ As ₂ Epitaxial Films Grown on (La,Sr)(Al,Ta)O ₃ Substrates without Buffer Layers. <i>Applied Physics Express</i> , 2010 , 3, 063101	2.4	81
70	Fabrication and electron transport properties of epitaxial films of electron-doped 12CaO \cdot Al ₂ O ₃ and 12SrO \cdot Al ₂ O ₃ . <i>Journal of Solid State Chemistry</i> , 2010 , 183, 385-391	3.3	17
69	Interface atomic structure of LaCuOSe:Mg epitaxial thin film and MgO substrate. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010 , 173, 229-233	3.1	2
68	Impurities in FeAs-based superconductor, SrFe ₂ As ₂ , studied by first-principles calculations. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010 , 173, 244-247	3.1	4
67	Origin of high-density hole doping and anisotropic hole transport in a wide gap layered semiconductor LaCuOSe studied by first-principles calculations. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 1636-1641	1.6	6
66	Water-induced superconductivity in SrFe ₂ As ₂ . <i>Physical Review B</i> , 2009 , 80,	3.3	64
65	Pseudoisotropic upper critical field in cobalt-doped SrFe ₂ As ₂ epitaxial films. <i>Physical Review Letters</i> , 2009 , 102, 117004	7.4	99
64	Direct imaging of doped fluorine in LaFeAsO _{1-x} F _x superconductor by atomic scale spectroscopy. <i>Applied Physics Letters</i> , 2009 , 95, 193107	3.4	18
63	Pressure effects on T _c of iron-based layered superconductor LaTMPO (TM= Fe, Ni). <i>Journal of Physics: Conference Series</i> , 2009 , 150, 052075	0.3	2
62	Angular and field properties of the critical current and melting line of Co-doped SrFe ₂ As ₂ epitaxial films. <i>Superconductor Science and Technology</i> , 2009 , 22, 125011	3.1	23
61	Tin monoxide as an s-orbital-based p-type oxide semiconductor: Electronic structures and TFT application. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 2187-2191	1.6	185
60	Atomically-flat, chemically-stable, superconducting epitaxial thin film of iron-based superconductor, cobalt-doped BaFe ₂ As ₂ . <i>Solid State Communications</i> , 2009 , 149, 2121-2124	1.6	65
59	Layered mixed-anion compounds: Epitaxial growth, active function exploration, and device application. <i>Journal of the European Ceramic Society</i> , 2009 , 29, 245-253	6	17
58	Heteroepitaxial film growth of layered compounds with the ZrCuSiAs-type and ThCr ₂ Si ₂ -type structures: From Cu-based semiconductors to Fe-based superconductors. <i>Physica C: Superconductivity and Its Applications</i> , 2009 , 469, 657-666	1.3	37
57	Low Threshold Voltage and Carrier Injection Properties of Inverted Organic Light-Emitting Diodes with [Ca ₂₄ Al ₂₈ O ₆₄] ⁴⁺ (4e ⁻) Cathode and Cu ₂ Se Anode. <i>Journal of Physical Chemistry C</i> , 2009 , 113, 18379-18384	3.8	42
56	Epitaxial film growth and optoelectrical properties of layered semiconductors, LaMnXO (X=P, As, and Sb). <i>Journal of Applied Physics</i> , 2009 , 105, 073903	2.5	30
55	Coexistence of superconductivity and antiferromagnetic ordering in the layered superconductor SmFePO. <i>Physical Review B</i> , 2008 , 78,	3.3	29

54	Crystal Structures, Optoelectronic Properties, and Electronic Structures of Layered Oxychalcogenides $MCuOCh$ ($M = Bi, La$; $Ch = S, Se, Te$): Effects of Electronic Configurations of $M3+$ Ions. <i>Chemistry of Materials</i> , 2008 , 20, 326-334	9.6	227
53	p-channel thin-film transistor using p-type oxide semiconductor, SnO . <i>Applied Physics Letters</i> , 2008 , 93, 032113	3.4	491
52	Superconductivity in Epitaxial Thin Films of Co-Doped $SrFe_2As_2$ with Bilayered $FeAs$ Structures and their Magnetic Anisotropy. <i>Applied Physics Express</i> , 2008 , 1, 101702	2.4	101
51	Characterization of copper selenide thin film hole-injection layers deposited at room temperature for use with p-type organic semiconductors. <i>Journal of Applied Physics</i> , 2008 , 104, 113723	2.5	14
50	Heteroepitaxial growth and optoelectronic properties of layered iron oxyarsenide, $LaFeAsO$. <i>Applied Physics Letters</i> , 2008 , 93, 162504	3.4	88
49	Heteroepitaxial growth of layered semiconductors, $LaZnOPn$ ($Pn = P$ and As). <i>Thin Solid Films</i> , 2008 , 516, 5800-5804	2.2	36
48	Electrical and optical properties of copper-based chalcogenide thin films deposited by pulsed laser deposition at room temperature: Toward p-channel thin film transistor fabricable at room temperature. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008 , 205, 2007-2012	1.6	5
47	Low and small resistance hole-injection barrier for NPB realized by wide-gap p-type degenerate semiconductor, $LaCuOSe:Mg$. <i>Organic Electronics</i> , 2008 , 9, 890-894	3.5	28
46	Electronic and magnetic properties of layered $LnFePO$ ($Ln=La$ and Ce). <i>Journal of Physics and Chemistry of Solids</i> , 2008 , 69, 2916-2918	3.9	13
45	Apparent bipolarity and Seebeck sign inversion in a layered semiconductor: $LaZnOP$. <i>Physical Review B</i> , 2007 , 76,	3.3	27
44	Optoelectronic properties and electronic structure of $YCuOSe$. <i>Journal of Applied Physics</i> , 2007 , 102, 113714	2.5	18
43	Heavy hole doping of epitaxial thin films of a wide gap p-type semiconductor, $LaCuOSe$, and analysis of the effective mass. <i>Applied Physics Letters</i> , 2007 , 91, 012104	3.4	82
42	Nickel-based oxyphosphide superconductor with a layered crystal structure, $LaNiOP$. <i>Inorganic Chemistry</i> , 2007 , 46, 7719-21	5.1	245
41	Growth, structure and carrier transport properties of Ga_2O_3 epitaxial film examined for transparent field-effect transistor. <i>Thin Solid Films</i> , 2006 , 496, 37-41	2.2	142
40	Magnetic and carrier transport properties of Mn-doped p-type semiconductor $LaCuOSe$: An investigation of the origin of ferromagnetism. <i>Journal of Applied Physics</i> , 2006 , 100, 033717	2.5	20
39	Opto-electronic properties and light-emitting device application of widegap layered oxychalcogenides: $LaCuOCh$ ($Ch =$ chalcogen) and $La_2CdO_2Se_2$. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006 , 203, 2800-2811	1.6	45
38	Wide-gap layered oxychalcogenide semiconductors: Materials, electronic structures and optoelectronic properties. <i>Thin Solid Films</i> , 2006 , 496, 8-15	2.2	77
37	Iron-based layered superconductor: $LaOFeP$. <i>Journal of the American Chemical Society</i> , 2006 , 128, 10012-10014	6.4	1051

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26	Photonic materials utilizing naturally occurring nanostructures. <i>Journal of Photochemistry and Photobiology A: Chemistry</i> , 2004 , 166, 141-147	4.7	7
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24	Optical Properties and Two-Dimensional Electronic Structure in Wide-Gap Layered Oxychalcogenide: La ₂ CdO ₂ Se ₂ . <i>Journal of Physical Chemistry B</i> , 2004 , 108, 17344-17351	3.4	30
23	Natural nanostructures in ionic semiconductors. <i>Microelectronic Engineering</i> , 2004 , 73-74, 620-626	2.5	14
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20	Synthesis of single-phase layered oxychalcogenide La ₂ CdO ₂ Se ₂ : crystal structure, optical and electrical properties. <i>Journal of Materials Chemistry</i> , 2004 , 14, 2946		33
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16	Electrical and Optical Properties and Electronic Structures of LnCuOS (Ln = La~Nd). <i>Chemistry of Materials</i> , 2003 , 15, 3692-3695	9.6	84
15	Intrinsic excitonic photoluminescence and band-gap engineering of wide-gap p-type oxychalcogenide epitaxial films of LnCuOCh (Ln=La, Pr, and Nd; Ch=S or Se) semiconductor alloys. <i>Journal of Applied Physics</i> , 2003 , 94, 5805-5808	2.5	74
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13	Preparation of transparent p-type (La _{1-x} Sr _x O)CuS thin films by r.f. sputtering technique. <i>Thin Solid Films</i> , 2002 , 411, 125-128	2.2	71
12	Preparation of highly conductive, deep ultraviolet transparent Ga ₂ O ₃ thin film at low deposition temperatures. <i>Thin Solid Films</i> , 2002 , 411, 134-139	2.2	237
11	Heteroepitaxial growth of single-phase zinc blende ZnS films on transparent substrates by pulsed laser deposition under H ₂ S atmosphere. <i>Solid State Communications</i> , 2002 , 124, 411-415	1.6	18
10	Electrical conductivity control in transparent p-type (LaO)CuS thin films prepared by rf sputtering. <i>Journal of Applied Physics</i> , 2002 , 91, 9177-9181	2.5	60
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6	Pulsed laser deposition system for producing oxide thin films at high temperature. <i>Review of Scientific Instruments</i> , 2001 , 72, 3340-3343	1.7	17
5	Electrical and Optical Properties of Radio-Frequency-Sputtered Thin Films of (ZnO) ₅ In ₂ O ₃ . <i>Chemistry of Materials</i> , 1998 , 10, 3033-3039	9.6	85
4	Improvement in thermoelectric properties of (ZnO) ₅ In ₂ O ₃ through partial substitution of yttrium for indium. <i>Journal of Materials Research</i> , 1998 , 13, 523-526	2.5	70
3	Thermoelectric Properties of (ZnO) ₅ In ₂ O ₃ Thin Films Prepared by r.f. Sputtering Method.. <i>Funtai Oyobi Fumatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy</i> , 1997 , 44, 44-49	0.2	28
2	Transparent Conducting Properties in Layered Oxychalcogenides. <i>Ceramic Transactions</i> , 466-473	0.1	
1	Electronic and Lattice Thermal Conductivity Switching by 3D~2D Crystal Structure Transition in Nonequilibrium (Pb _{1-x} Sn _x)Se. <i>Advanced Electronic Materials</i> , 2200024	6.4	1

